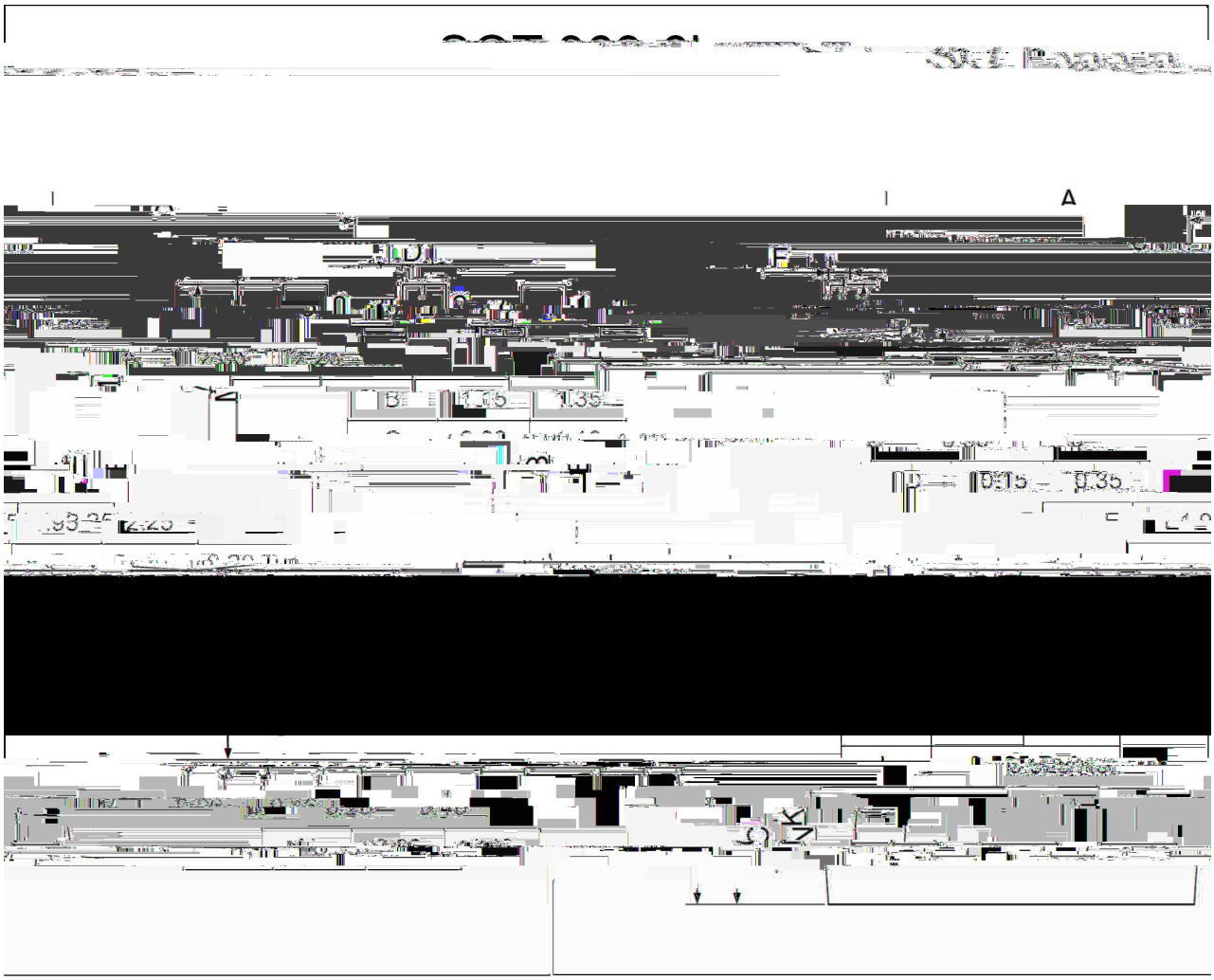
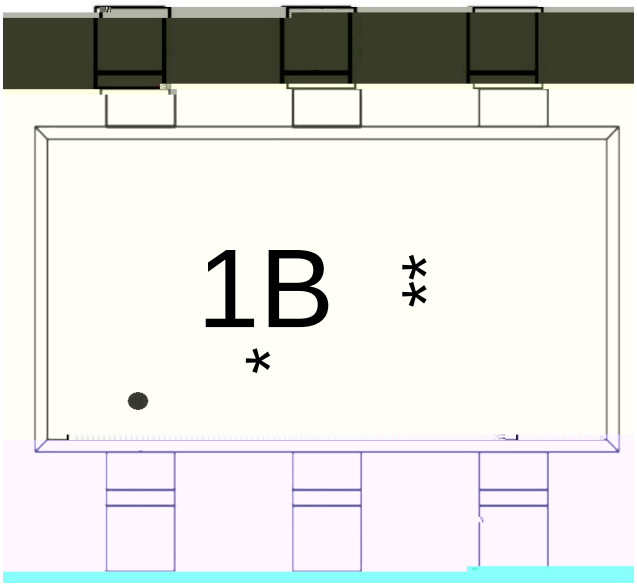
silicon NPN transistor in a SOT-363 Plastic Package.

High voltage, complementary pair with BRDBC856WS, HF Product.

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	80	V
Collector to Emitter Voltage	V_{CEO}	65	V
Emitter to Base Voltage	V_{EBO}	6.0	V
Collector Current - Continuous	I_C	100	mA
Collector Power Dissipation	P_C	200	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector−Base Breakdown Voltage	V_{CBO}	I_C =10 A I_E	80			V
Collector−Emitter Breakdown Voltage	V_{CEO}	I_C =10mA I_B = 0	65			V
Emitter−Base Breakdown Voltage	V_{EBO}	I_E =10 A I_C = 0	6.0			V
Collector Cut-Off Current	I_{CBO}	V_{CB}=30V I_E=0			15	nA
Emitter Cut-Off Current	I_{EBO}	V_{EB}=5V I_C=0			500	nA
DC Current Gain	h_{FE}	V_{CE}=5.0V I_C=2.0mA	110		450	
Collector to Emitter Saturation Voltage	$V_{CE(sat)(1)}$	I_C=10mA I_B=0.5mA			0.1	V
	$V_{CE(sat)(2)}$	I_C=100mA I_B=5.0mA			0.3	V
Base to Emitter Saturation Voltage	$V_{BE(sat)}$	I_C=10mA I_B=0.5mA		0.77		V
Transition Frequency	f_T	V_{CB}=5.0V I_E=10mA f=100MHz				





h_{FE}

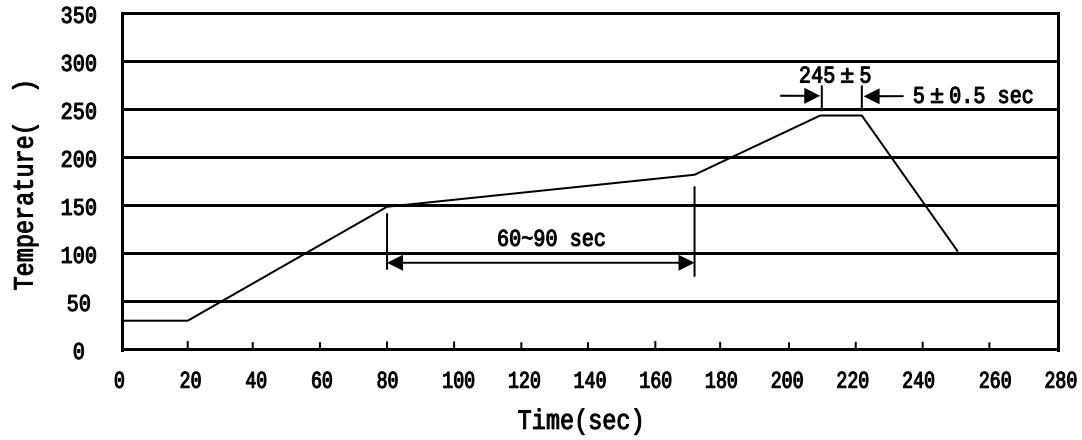
Note:

1 Product Type Code

h_{FE} Classifications Symbol Code

Lot No. Code, code change with Lot No

Temperature Profile for IR Reflow Soldering(Pb-Free)



	Note:
1 150 180 60 90sec;	1.Preheating:150~180 , Time:60~90sec.
2 245 5 5 0.5sec;	2.Peak Temp.:245 5 , Duration:5 0.5sec.
3 2 10 /sec.	3. Cooling Speed: 2~10 /sec.

260 5 10 1 sec. Temp.:260±5 Time:10±1 sec

/ REEL

Package Type	Units					Dimension		(unit mm³)
	Units/Reel /	Reels/Inner Box /	Units/Inner Box /	Inner Boxes/Outer Box /	Units/Outer Box /	Reel	Inner Box	Outer Box
SOT-363	3,000	10	30,000	6	180,000	7 ×8	180×120×180	390×385×205